
2SK1624(L), 2SK1624(S)

Silicon N-Channel MOS FET

HITACHI

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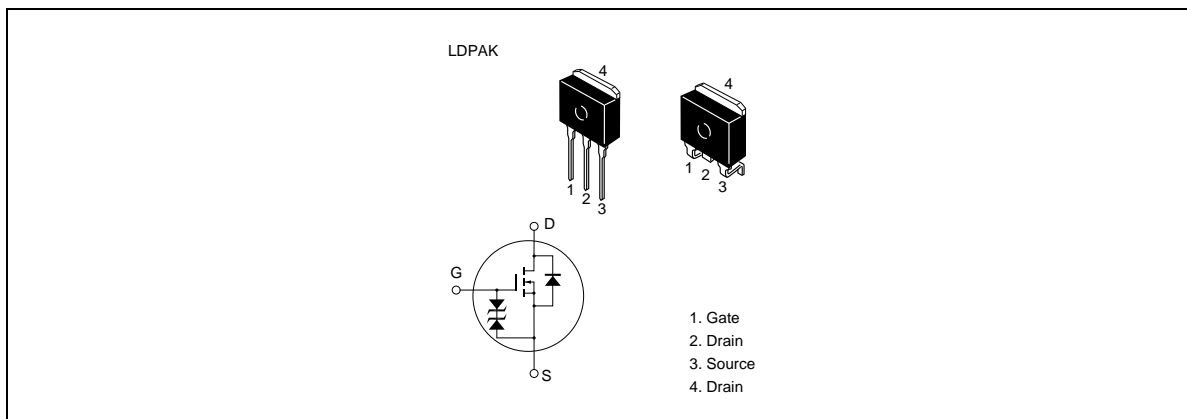
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



2SK1624(L), 2SK1624(S)

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|---|---------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 600 | V |
| Gate to source voltage | V_{GSS} | ±30 | V |
| Drain current | I_D | 4 | A |
| Drain peak current | $I_{D(pulse)}^{*1}$ | 16 | A |
| Body to drain diode reverse drain current | I_{DR} | 4 | A |
| Channel dissipation | Pch^{*2} | 50 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

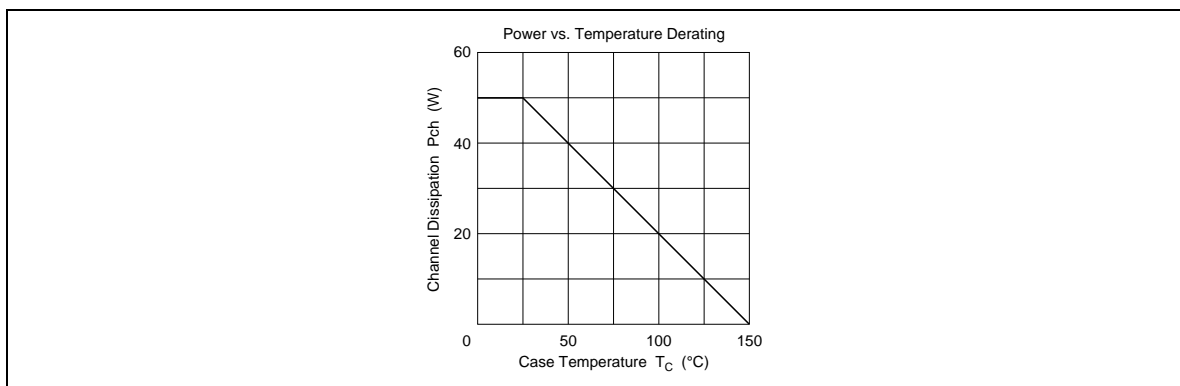
2SK1624(L), 2SK1624(S)

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--|---------------|-----|-----|-----|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 600 | — | — | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±30 | — | — | V | $I_G = \pm 100 \mu\text{A}, V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ±10 | μA | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 250 | μA | $V_{DS} = 500 \text{ V}, V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | — | 3.0 | V | $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ |
| Static Drain to source on state resistance | $R_{DS(on)}$ | — | 1.8 | 2.4 | Ω | $I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$ |
| Forward transfer admittance | yfs | 2.2 | 3.5 | — | S | $I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$ |
| Input capacitance | Ciss | — | 600 | — | pF | $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ |
| Output capacitance | Coss | — | 140 | — | pF | $f = 1 \text{ MHz}$ |
| Reverse transfer capacitance | Crss | — | 25 | — | pF | |
| Turn-on delay time | $t_{d(on)}$ | — | 8 | — | ns | $I_D = 2 \text{ A}, V_{GS} = 10 \text{ V},$ |
| Rise time | t_r | — | 30 | — | ns | $R_L = 15 \Omega$ |
| Turn-off delay time | $t_{d(off)}$ | — | 60 | — | ns | |
| Fall time | t_f | — | 35 | — | ns | |
| Body to drain diode forward voltage | V_{DF} | — | 0.9 | — | V | $I_F = 4 \text{ A}, V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t_{rr} | — | 300 | — | ns | $I_F = 4 \text{ A}, V_{GS} = 0,$ $di_f/dt = 100 \text{ A}/\mu\text{s}$ |

Note 1. Pulse test

See characteristic curves of 2SK1402.



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